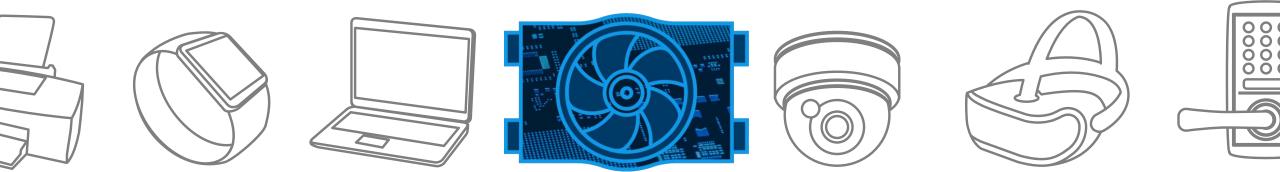


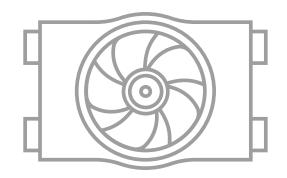
Automotive Radiator Fan Solution Proposal by Toshiba



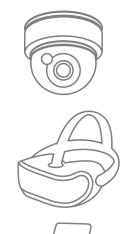
R21



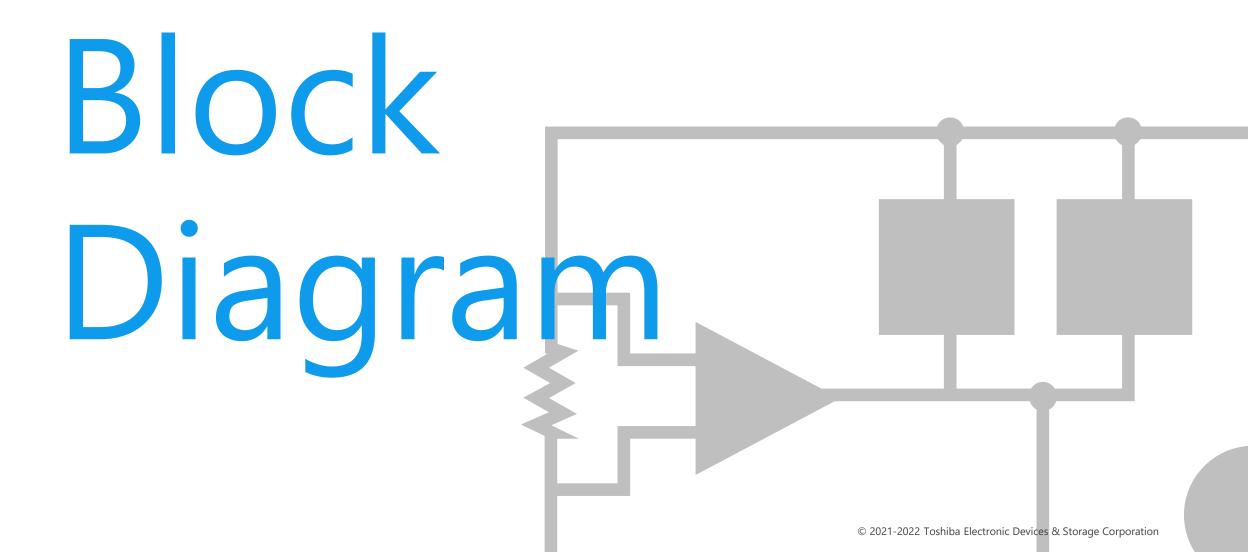




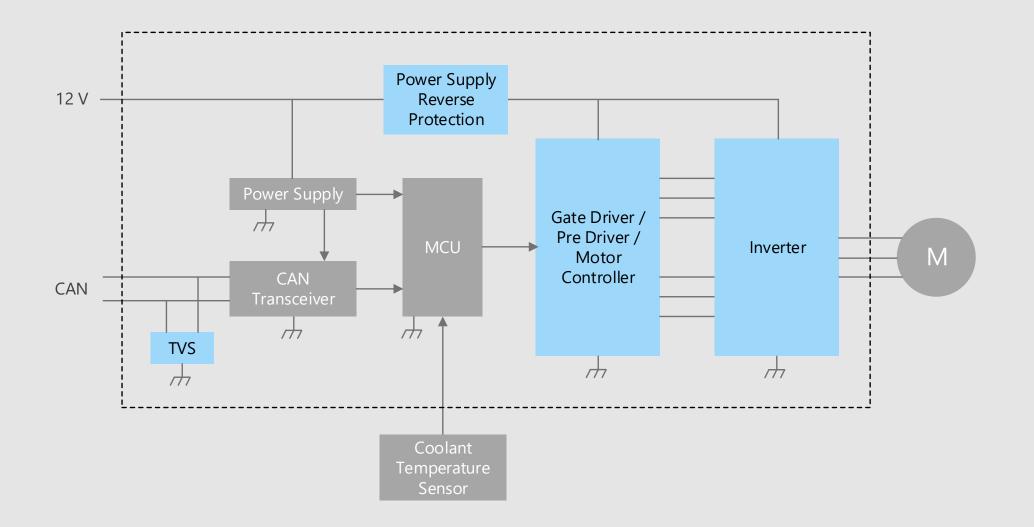
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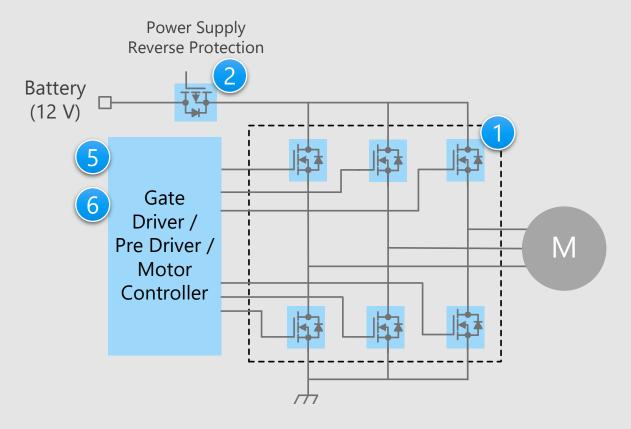


Radiator Fan Overall block diagram



Radiator Fan Detail of driving circuit for brushless DC motor

Driving circuit for brushless DC motor



* Click on the numbers in the circuit diagram to jump to the detailed descriptions page

Criteria for device selection

- It is necessary to select the product with the suitable voltage and current ratings for each application.
- It is necessary to select a gate driver according to the characteristics of the switching device to be driven.
- A small surface mount package is suitable for realizing miniaturization of the ECU.

Proposal from Toshiba

- Low on-resistance contributes to low power consumption of the system U-MOS Series 40 V N-ch MOSFET
 U-MOS Series -40 V / -60 V P-ch MOSFET
- Gate driver with protection diagnostic function

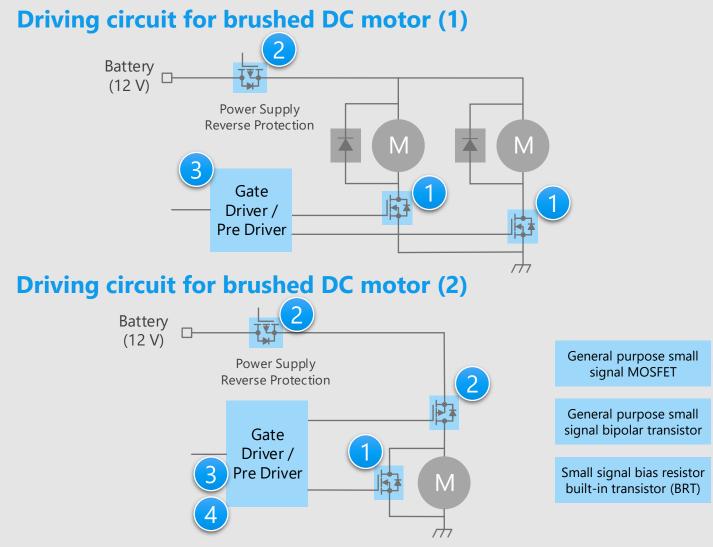
Gate driver (for motor)

 Full bridge pre driver compliant with automotive functional safety standard Brushless DC motor pre driver

5)

6

Radiator Fan Details of driving circuit for brushed DC motor



* Click on the numbers in the circuit diagram to jump to the detailed descriptions page

Criteria for device selection

- It is necessary to select the product with the suitable voltage and current ratings for each application.
- It is necessary to select a gate driver according to the characteristics of the switching device to be driven.
- A small surface mount package is suitable for realizing miniaturization of the ECU.

Proposal from Toshiba

 Low on-resistance contributes to low power consumption of the system U-MOS Series 40 V N-ch MOSFET U-MOS Series -40 V / -60 V P-ch MOSFET
 Realize driving circuit for brushed DC

2

8

motor easily

Gate driver (for switch) Brushed DC motor pre driver

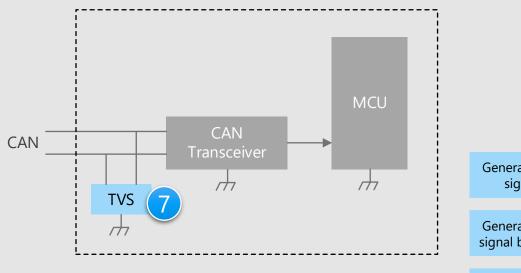
- Extensive product lineup

8

General purpose small signal MOSFET General purpose small signal bipolar transistor Small signal bias resistor built-in transistor (BRT) 10

Radiator Fan Detail of CAN transceiver circuit

CAN transceiver circuit



General purpose small signal MOSFET

(8)

9

10

General purpose small signal bipolar transistor

Small signal bias resistor built-in transistor (BRT)



- A small surface mount package is suitable for realizing miniaturization of the ECU.

Proposal from Toshiba

- Suitable for ESD protection

TVS diode (for CAN communication)

- Extensive product lineup

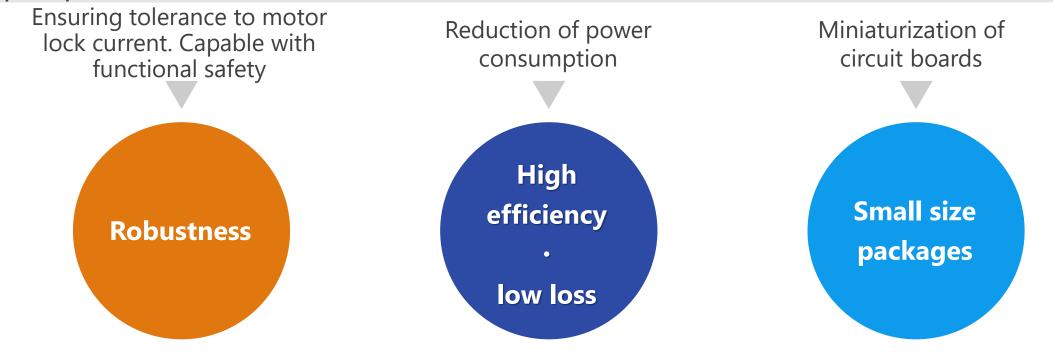
General purpose small signal MOSFET General purpose small signal bipolar transistor Small signal bias resistor built-in transistor (BRT) 10

* Click on the numbers in the circuit diagram to jump to the detailed descriptions page

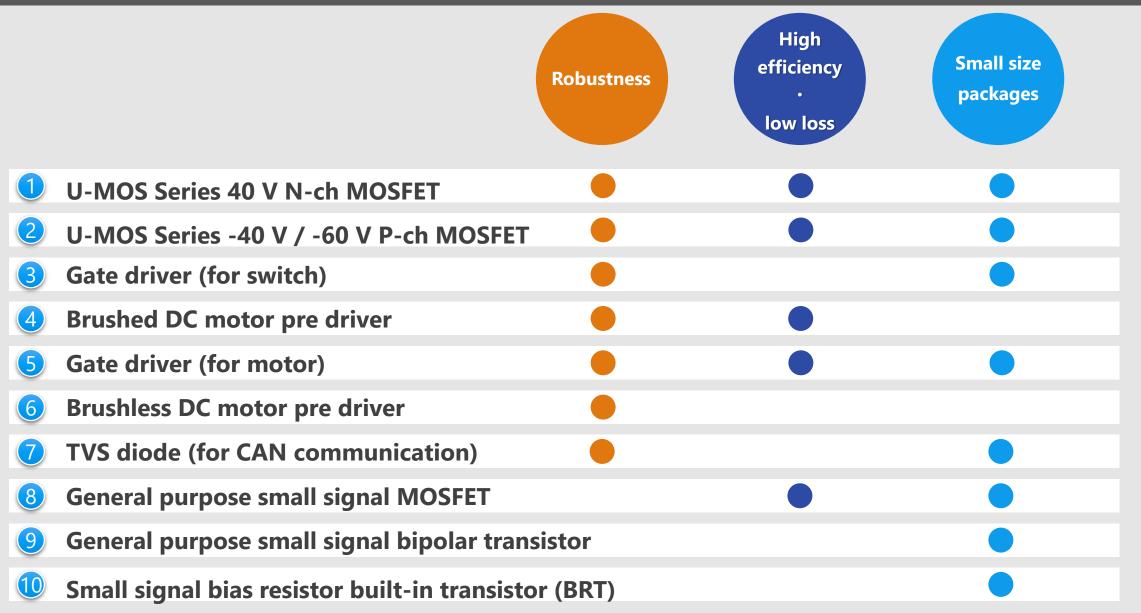
Recommended Devices

Device solutions to address customer needs

As described above, in the design of radiator fan, **"Ensuring tolerance to motor lock current. Capable with functional safety**", **"Reduction of power consumption**" and **"Miniaturization of circuit boards**" are important factors. Toshiba's proposals are based on these three solution perspectives.



Device solutions to address customer needs



Post (solder connection)

S-TOGL[™] &

Cu connector

: 400 ns / div

Value provided

The latest processes enables low on-resistance and low noise, thereby reducing power consumption.

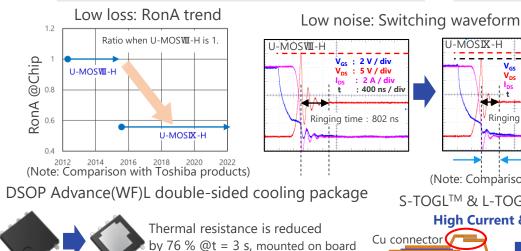
Low loss

(reduced on-resistance)

Using low on-resistance technology to contribute to reduced power consumption systems.

On-resistance of 44 % reduction per unit area. (compared to Toshiba's U-MOSWII-H products)

Compared to Toshiba's SOP Advance(WF)



Small and low loss package

By adopting a Cu clip structure and a doublesided heat dissipation structure, low loss and high heat dissipation are realized. Wettable Flank (WF) package contributes to good mountability.

Postless

Low V_{DS} peak



Low noise (low EMI)

Improved chip process reduces surge voltage and ringing time.

		MOS ₩ -H	Lineup				
		MOSIX-H	Part number	Rated drain current [A]	On-resistance (Max) [mΩ] @V _{GS} = 10 V	Package	
	I _{DS} : 2 A / div t : 400 ns / div		XPN3R804NC	40	3.8	TSON Advance(WF)	•
	Ringing time : 468 ns		TK1R4S04PB	120	1.35	DPAK+	•
			XPHR7904PS	150	0.79	SOP Advance(WF)	
	Short ringing		TPWR7904PB	150	0.79	DSOP Advance(WF)L	\diamond
	Note: Comparison with Toshiba p		XPJR6604PB*	(200)	(0.66)	S-TOGL [™]	(11)
	GL™ & L-TOGL™ Cu clip st		XPQR3004PB	400	0.30	L-TOGL [™]	
cto	High Current & Low resistan	* : Under development (\	/alues enclosed in par	entheses are tentative specifica	ations. Specifications are subject to	change without notice	

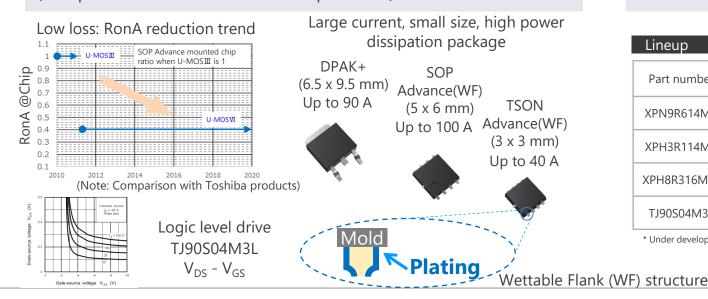


Low on-resistance contributes to reduce system power consumption.

Low loss (reduced on-resistance) and logic level drive

Using a low on-resistance technology contributes to reduce system power consumption.

A lineup of logic level drive type is supported. The on-resistance per area is reduced by 60 %. (compared to Toshiba's U-MOSII products)





Small and low loss packages

By adopting a Cu connector structure, a low loss and high power dissipation package is realized. Wettable Flank (WF) package contributes to good mountability.

Lineup									
Part number	Rated drain-source voltage [V]	Rated drain current [A]	On-resistance (Max) $[m\Omega] @V_{GS} = -10 V$	Package					
XPN9R614MC	-40	-40	9.6	TSON Advance(WF)					
XPH3R114MC	-40	-100	3.1						
XPH8R316MC*	-60	(-90)	(8.3)	SOP Advance(WF)					
TJ90S04M3L	-40	-90	4.3	DPAK+					

* Under development (Values enclosed in parentheses are tentative specifications. Specifications are subject to change without notice.)



Robustness High efficiency Low loss Small size package

Value provided

A charge pump circuit for the N-ch MOSFET gate drive is built in, allowing for easy semiconductor relay configuration.

Built-in charge pump circuit

Built-in charge pump circuit enables N-ch MOSFET as high side switch. Easy to configure a semiconductor relay.



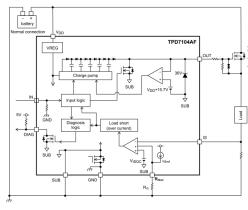
It is possible to be controlled directly by output signal of MCUs or CMOS logic ICs.



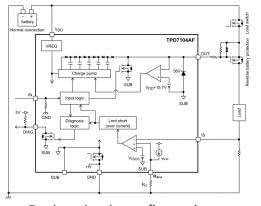
Small package

The small surface mount packages such as PS-8, SSOP16 and WSON10A contribute to the miniaturization of equipment.

Semiconductor relay (switch) application (TPD7104AF)



Power supply reverse connection protection MOSFET control (TPD7104AF)



Back to back configuration

Lineup

Part number	TPD7104AF	TPD7106F	TPD7107F
Package	PS-8 (2.8 x 2.9 mm)	SSOP16 (5.5 x 6.4 mm)	WSON10A (3 x 3 mm)
Function	High side gate driver	High side gate driver	High side gate driver
Output	1	1	1
Features	Operating power supply voltage range: 5 to 18 V Built-in power supply reverse connection protection function (Protective MOSFET control with back-to-back circuitry)	Operating power supply voltage range: 4.5 to 27 V Built-in power supply reverse connection protection function (Protective MOSFET control with back-to-back circuitry)	 Operating power supply voltage range: 5.75 to 26 V Current sense output Protective functions; overcurrent, overtemperature, GND disconnect, etc. reverse battery connection Diagnosis output; overcurrent, load open, overtemperature, etc.



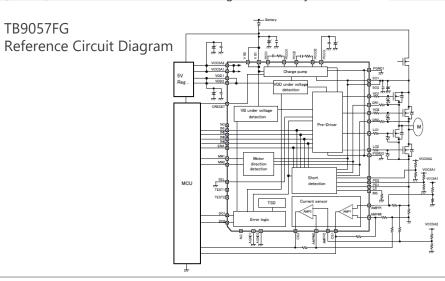


Compliant with automotive functional safety standard (ISO 26262 : ASIL-D) and motor current detecting function is built in.

Compliant with automotive functional safety standard

Compliant with ISO26262 ASIL-D. [Note1] FMEDA [Note2] and safety manuals can be provided.

[Note1] Automotive Safety Integrity Level [Note2] Failure Modes Effects and Diagnostics Analysis





Two channels of motor current detection amplifiers are built in to make them redundant.



AEC-Q100 qualified

It is AEC-Q100 qualified and it can be used for various automotive applications.

Lineup					
	Part number	TB9057FG			
	Package	LQFP48-P-0707-0.50C			
	Package body size	7.0 x 7.0 mm			
	Control method	Direct			
	External MOSFET (High side / Low side)	N-ch / N-ch			
Function	Detection of overheating, low voltage and short circuit	\checkmark			
	Output of detection function diagnosis result	\checkmark			



Robustness High efficiency Low loss Small size package

Value provided

The high gate drive current capability reduces MOSFET losses and improves the efficiency of system.

High gate drive current

High drive current capability and high speed switching contribute to reduce the loss.

TPD7211F: ±0.5 A TPD7212F, TPD7212FN: -1 / +1.5 A 2 ^B

Built-in protection / diagnostic output function

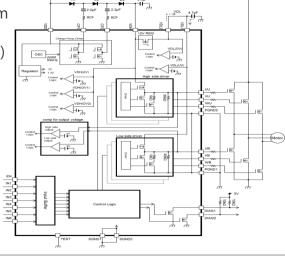
MOSFET is turn off when a signal is input that causes arm short circuit. Functions to monitor abnormalities of the power supply voltage and output voltage are built in.



Small surface mount package

PS-8, WQFN32 and SSOP30 are small surface mount packages. They contribute to the miniaturization of system.

Example of application and block diagram	_	
of TPD7212F, TPD7212FN		Charge
(Three phase brushless DC motor control)	OSC M	
	Regulator	/ 2V ontrol ←



Lineup				
Part number	TPD7211F	TPD7212F / TPD7212FN		
Function Half bridge output gate driver Gate		Gate driver for three-phase brushless motor		
Number of output 2 outputs		6 outputs		
Package		TPD7212F Back surface		
	PS-8 (2.8 x 2.9 mm)	P-WQFN32-0505-0.50-002 SSOP30-P-300-0.65		
Features	•For high side P-ch MOSFET drive	 For driving high side N-ch MOSFET (with built-in charge pumps) Built-in voltage monitoring function (power supply, output) 		



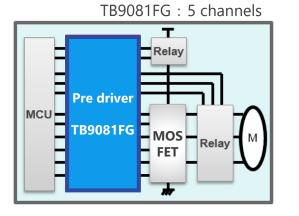
Compliant with automotive functional safety standard (ISO 26262 : ASIL-D) and safety relay drivers are built in.

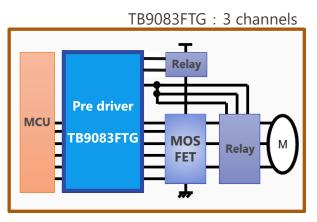
Compliant with automotive functional safety standard

Compliant with ISO 26262 ASIL-D. [NOTE 1] FMEDA [NOTE 2] and safety manuals can be provided.

[NOTE 1] Automotive Safety Integrity Level [NOTE 2] Failure Modes Effects and Diagnostics Analysis

Built-in safety relay drivers





Built-in safety relay drivers and motor current detection
amplifiers

The safety relay drivers are built in for the power supply side MOSFETs and the motor phase cut MOSFETs. In addition, a 3 channels of motor current detection amplifiers are built in to support 3 shunts.

Linou



AEC-Q100 qualified

It is AEC-Q100 qualified and it can be used for various automotive applications.

	Part number	TB9081FG	TB9083FTG
Package Package body size		LQFP64	VQFN48
		10.0 x 10.0 mm	7.0 x 7.0 mm
Operating ambient temperature		Ta = -40 to 125 °C	Ta = -40 to 150 °C
	Control method	Direct	Direct
	External MOSFET (High side / Low side)	N-ch / N-ch	N-ch / N-ch
Function	Detection of overheating, low voltage and short circuit	√	✓
	Output of detection function diagnosis result	✓ (BIST [Note 3])	✓ (BIST)

[Note 3] Built-in Self Test



Robustness High efficiency . Low loss Small size package

Value provided

TVS diodes prevent system damage and malfunction caused by electrostatic discharge (ESD).

Improve ESD pulse absorbability

Toshiba proprietary Zener process improves the ESD pulse absorption of TVS diodes. (Achieving both low dynamic resistance R_{DYN} and low capacitance between terminals C_t)

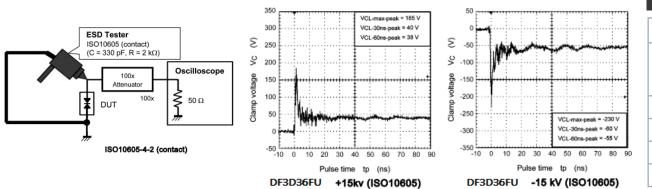


These are products applicable to invehicle LAN communication such as CAN, CAN FD and FlexRay.



High ESD immunity

 $V_{ESD} > \pm 30 \text{ kV} @$ ISO 10605 $V_{ESD} > \pm 20 \text{ kV} @$ IEC 61000-4-2 (Level 4)



Part number	DF3D18FU	DF3D36FU		
Package	USM (SOT-323)			
V _{ESD} [kV] @ISO 10605	±30	±30	±20	
V _{RWM} (Max) [V]	12	24	28	
C _t (Typ. / Max) [pF]	9 /	6.5 / 8		
R _{DYN} (Typ.) [Ω]	0.8	1.1	1.5	

(Note) The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted. This product is an ESD protection diode and cannot be used for purposes other than ESD protection.



Wide lineup of small packages contribute to reduce the size and power consumption of system.

Small package

A lineup of various small packages such as SOT-723 (VESM 1.2 x 1.2 mm package) is available, contributing to reduce mounting area.

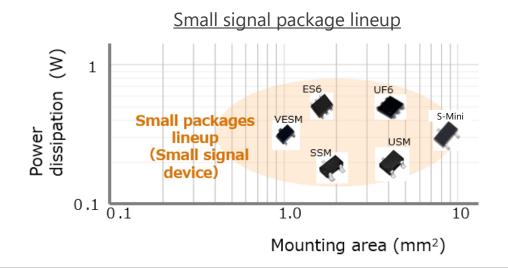


SSM3J66MFV can be driven at low gatesource voltage of 1.2 V.



AEC-Q101 qualified

AEC-Q101 qualified and can be used for various automotive applications.



Lineup

Part number Package V _{DSS} [V]		SSM3K7002KF	SSM3J168F	SSM3J66MFV
		S-Mini (SOT-346)	S-Mini (SOT-346)	VESM (SOT-723)
		60	-60	-20
I _D [A]	I _D [A]		-0.4	-0.8
R _{DS(ON)}	Тур.	1.2	1.4	0.31
$@ V_{GS} = 4.5 V [\Omega]$ Max Drive voltage [V]		1.75	1.9	0.39
		4.5	-4.0	-1.2
Polarity		N-ch	P-ch	P-ch





Extensive product lineup to meet customers' needs.

Extensive lineup of packages

Various packages such as 1-in-1, 2-in-1 are provided and suitable products for circuit board design are selectable.

Extensive product lineup

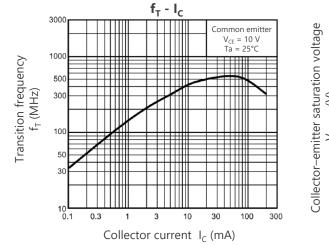
Various product lineups, such as general purpose, low noise, low $V_{CE(sat)}$ and high current types are provided. Products can be selected in accordance with the application.

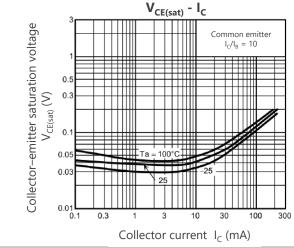


AEC-Q101 qualified

AEC-Q101 qualified and can be used for various automotive applications.

Characteristic examples of 2SC2712





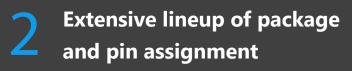
Package		SOT	-23F		OT-323) DT-323F)*	S-Mini (S	SOT-346)	
Classification	V _{CEO} [V]	I _c [mA]	NPN	PNP	NPN	PNP	NPN	PNP
Concerclanation	50	150			2SC4116	2SA1586	2SC2712	2SA1162
General purpose	50	500					2SC3325	2SA1313
Low noise	120	100			2SC4117	2SA1587	2SC2713	2SA1163
	50	1700				2SA2195*		
High current	50	2000		TTA501				
	50	2500	TTC501					



Extensive product lineup to meet customers' needs.

Built-in bias resistor type (BRT : Bias Resistor built-in Transistor)

The BRTs contribute to reduction of the number of components, assembly workload and mounting area of circuit boards.

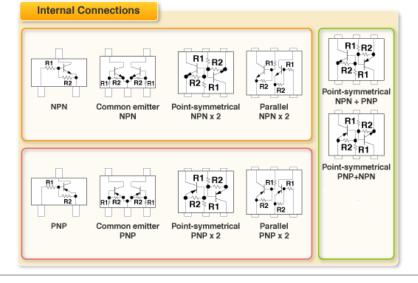


Various package lineups, such as 1-in-1, 2-in-1 and various pin assignment type are provided and suitable products for circuit board design are selectable.



AEC-Q101 qualified

AEC-Q101 qualified and can be used for various automotive applications.



Lineup	Lineup								
	Part number	NPN (BRT)	PNP (BRT)						
Dackago	ES6 (SOT-563)	RN1907FE	RN2907FE						
Package	US6 (SOT-363)	RN1901	RN2901						
	V _{CEO} [V]	50	-50						
	I _C [mA]	100	-100						

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